

# HSK120

Silicon Epitaxial Planar Diode for High Speed Switching

# HITACHI

ADE-208-171C(Z)

Rev 3

Jan. 1999

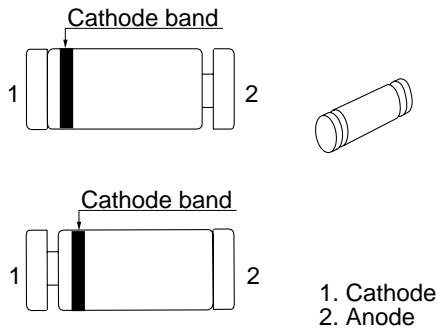
## Features

- Low reverse recovery time. ( $t_{rr} = 3.0\text{ns}$  max)
- LLD package is suitable for high density surface mounting and high speed assembly

## Ordering Information

Type No.	Cathode band	Package Code
HSK120	White	LLD

## Outline



**Absolute Maximum Ratings (Ta = 25°C)**

Item	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}$	70	V
Reverse voltage	$V_R$	60	V
Peak forward current	$I_{FM}$	450	mA
Non-Repetitive peak forward surge current	$I_{FSM}^{*1}$	4	A
Average rectified current	$I_O$	150	mA
Junction temperature	$T_j$	175	°C
Storage temperature	$T_{stg}$	-65 to +175	°C

Note 1. Within 1μs forward surge current..

**Electrical Characteristics (Ta = 25°C)**

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_F$	—	—	0.8	V	$I_F = 10\text{ mA}$
Reverse voltage	$V_R$	70	—	—	V	$I_R = 5\mu\text{A}$
Reverse current	$I_R$	—	—	0.1	μA	$V_R = 60\text{V}$
Capacitance	$C$	—	—	3.0	pF	$V_R = 0\text{V}, f = 1\text{ MHz}$
Reverse recovery time	$t_{rr}$	—	—	3.0	ns	$I_F = 10\text{ mA}, V_R = 6\text{V}, R_L = 50\Omega, I_{rr} = 0.1I_R$

Main Characteristic

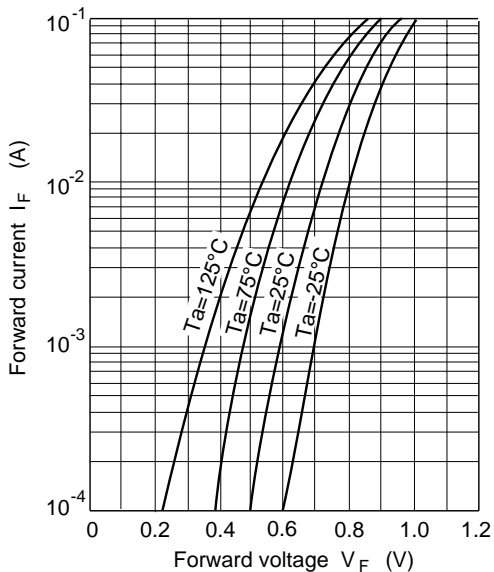


Fig.1 Forward current Vs. Forward voltage

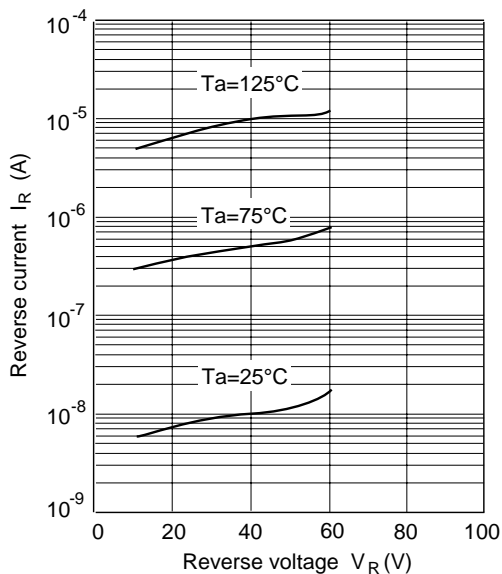


Fig.2 Reverse current Vs. Reverse voltage

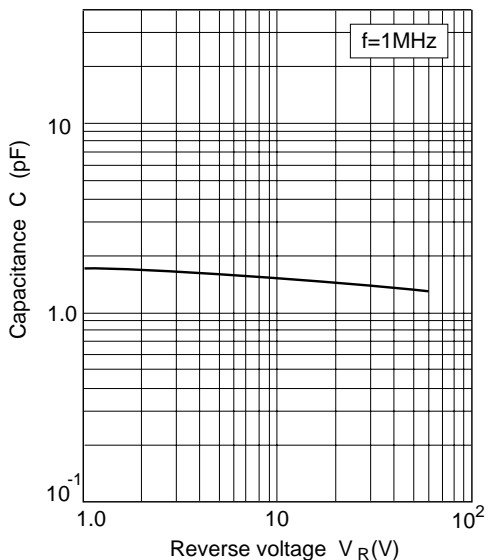
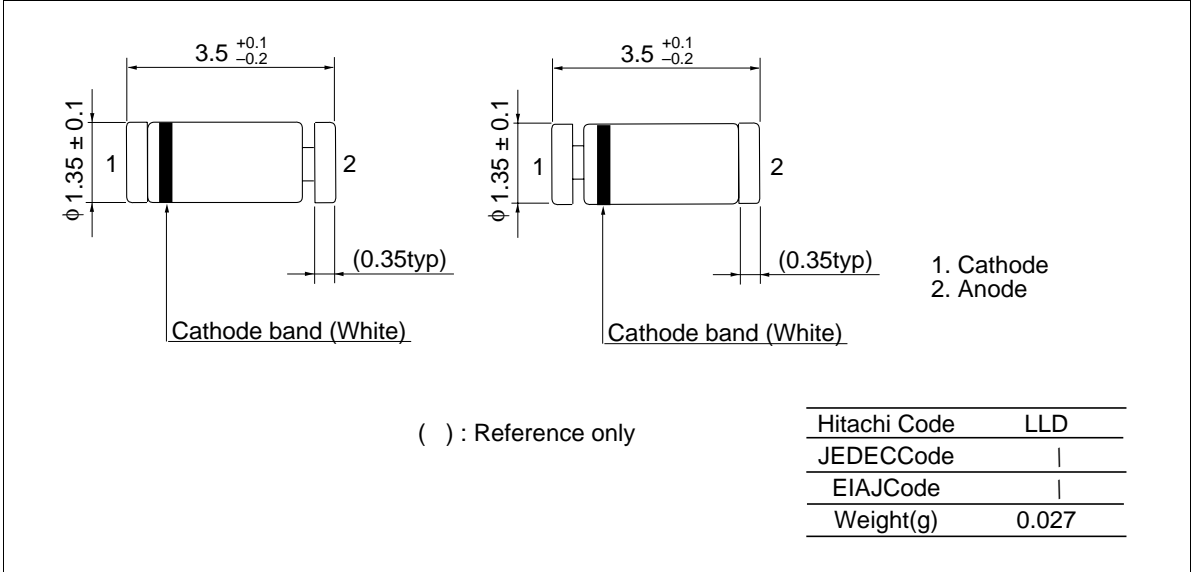


Fig.3 Capacitance Vs. Reverse voltage

## Package Dimensions

Unit : mm



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